JJMICROELECTRONICS

80V, 285A, 1.4mΩ N-channel Power SGT MOSFET

JMSH0802MTL

Features

- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED
- 100% ΔVds TESTED
- Halogen-free; RoHS-compliant
- Pb-free plating

Applications

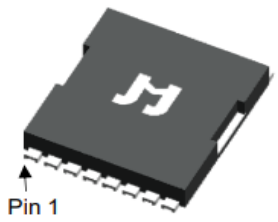
- Load Switch
- PWM Application
- Power Management

Product Summary

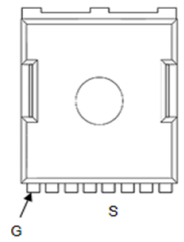
Parameters	Value	Unit
V_{DSS}	80	V
$V_{GS(th)\_Typ}$	2.9	V
I_D(@V_{GS}=10V)	285	A
$R_{DS(ON)\_Typ}$(@V_{GS}=10V	1.4	mΩ

RoHS

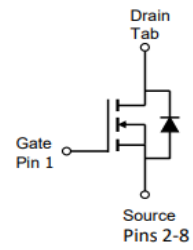
Pb Lead-free Green



PowerJE®10x12 Top View



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSH0802MTL	SH0802M	1	Tape&Reel	PowerJE®10x12	2000	10000

Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-to-Source Voltage		80	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	285	A
		T_C = 100°C	202	
I_{DM}	Pulsed Drain Current (1)		Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy (2)		1423	mJ
P_D	Power Dissipation	T_C = 25°C	310	W
		T_C = 100°C	124	
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(3)	34	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.4	

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	80	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 64V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.0	2.9	3.8	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(4)	V_{GS} = 10V, I_D = 20A	-	1.4	2.0	mΩ
Dynamic Characteristics						
R_g	Gate Resistance	f = 1MHz	-	0.4	-	Ω
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 40V, f = 1MHz	6243	8740	11799	pF
C_{oss}	Output Capacitance		1257	1760	2376	pF
C_{rss}	Reverse Transfer Capacitance		19	26	35	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V V_{DS} = 40V, I_D = 20A	91	128	173	nC
Q_{gs}	Gate Source Charge		29	40	54	nC
Q_{gd}	Gate Drain("Miller") Charge		18	26	34	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 39V I_D= 20A, R_{GEN} = 6.2Ω	-	36	-	ns
t_r	Turn-On Rise Time		-	38	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	87	-	ns
t_f	Turn-Off Fall Time		-	43	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	285	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	1140	A
V_{SD}	Body Diode Forward Voltage	V_{GS} = 0V, I_S = 20A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 20A, di/dt = 100A/us	94	127	178	ns
Qrr	Body Diode Reverse Recovery Charge		-	194	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25C, V_{DD}=40V, V_G=10V, R_G=25ohm, L=3mH, I_{AS}=30.8A, V_{DD}=0V during time in avalanche.
3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Typical Performance Characteristics

Figure 1: Power De-rating

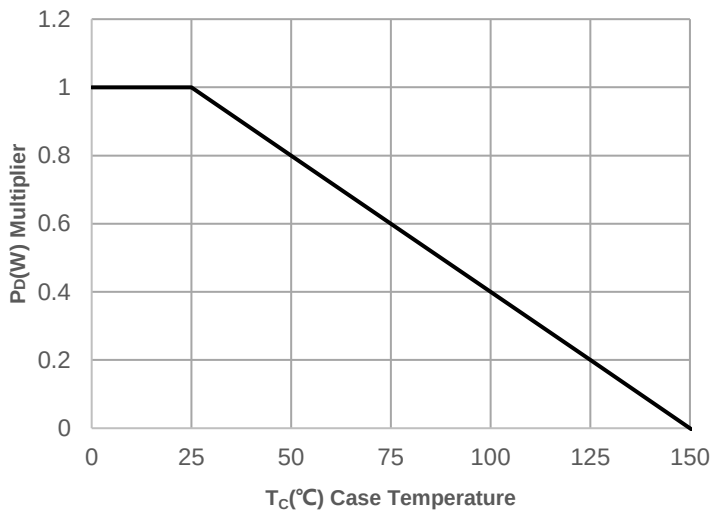


Figure 2: Current De-rating

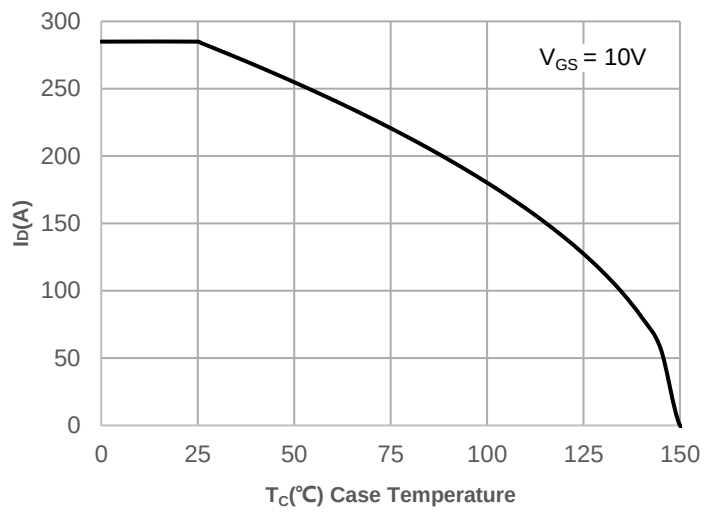


Figure 3: Normalized Maximum Transient Thermal Impedance

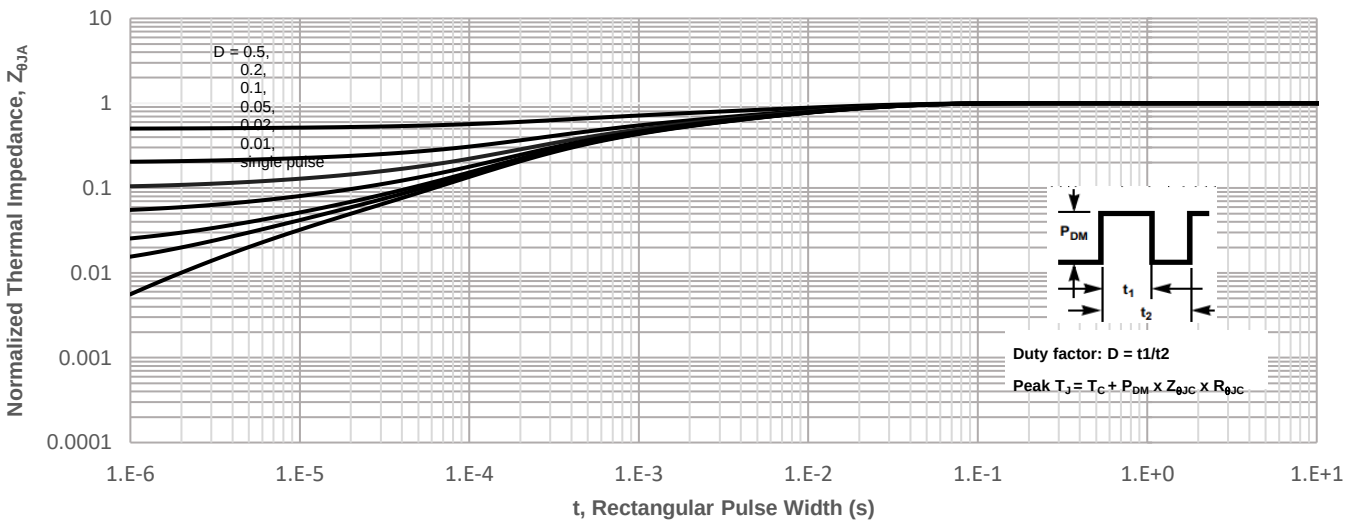
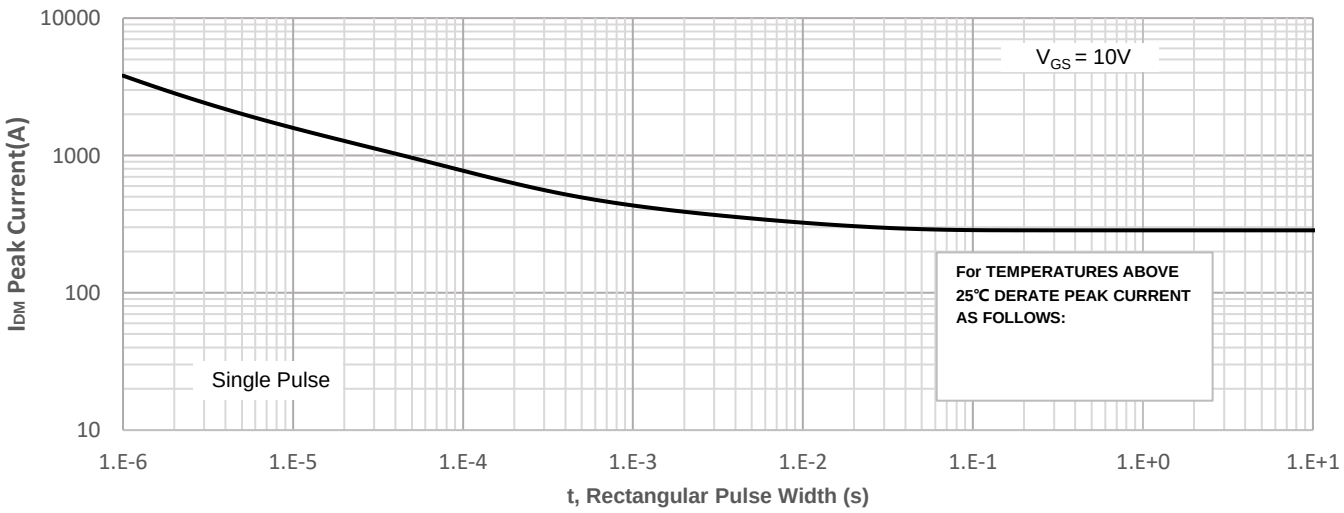


Figure 4: Peak Current Capacity



Typical Performance Characteristics

Figure 5: Output Characteristics

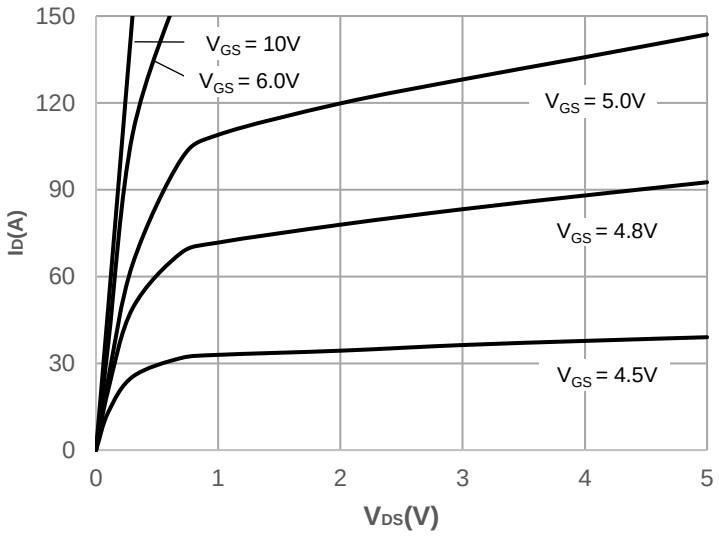


Figure 6: Typical Transfer Characteristics

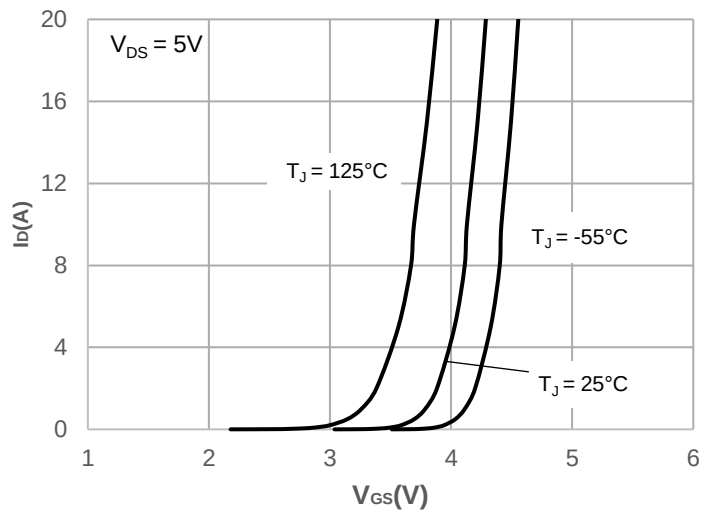


Figure 7: On-resistance vs. Drain Current

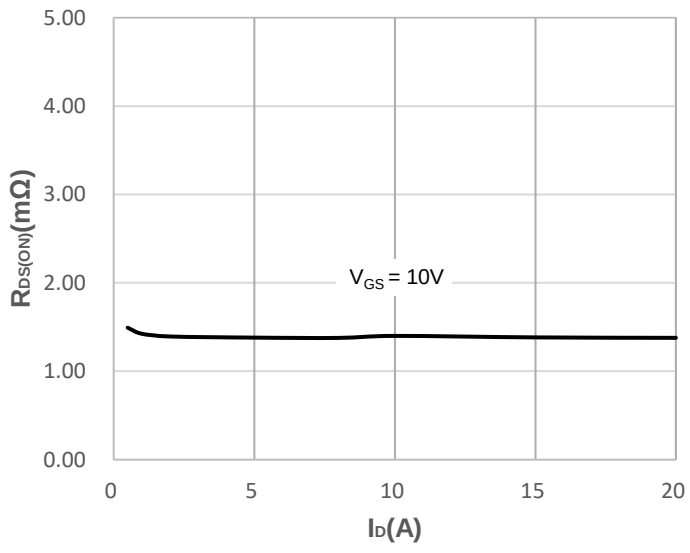


Figure 8: Body Diode Characteristics

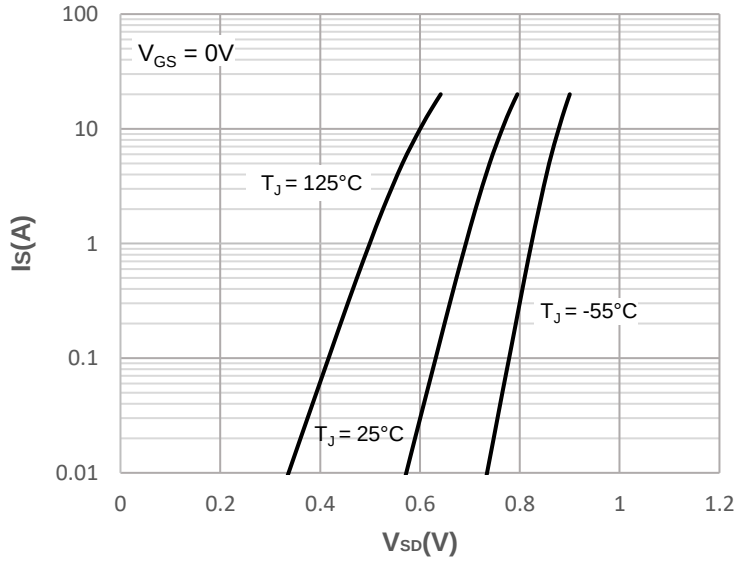


Figure 9: Gate Charge Characteristics

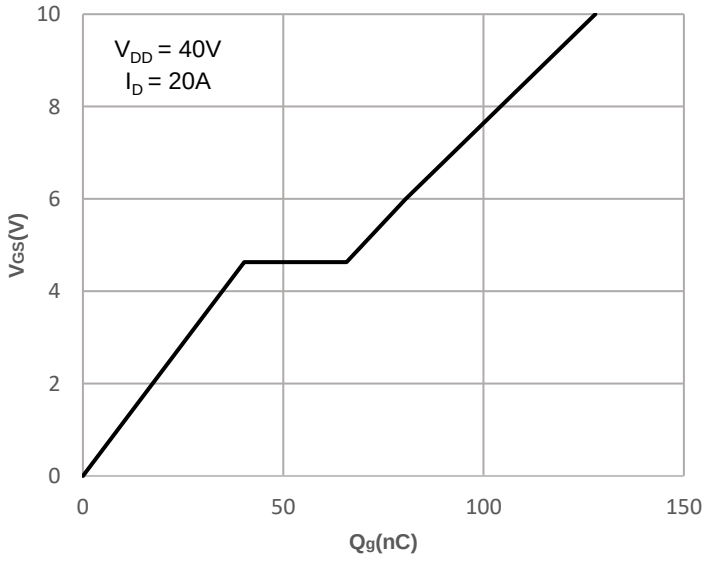
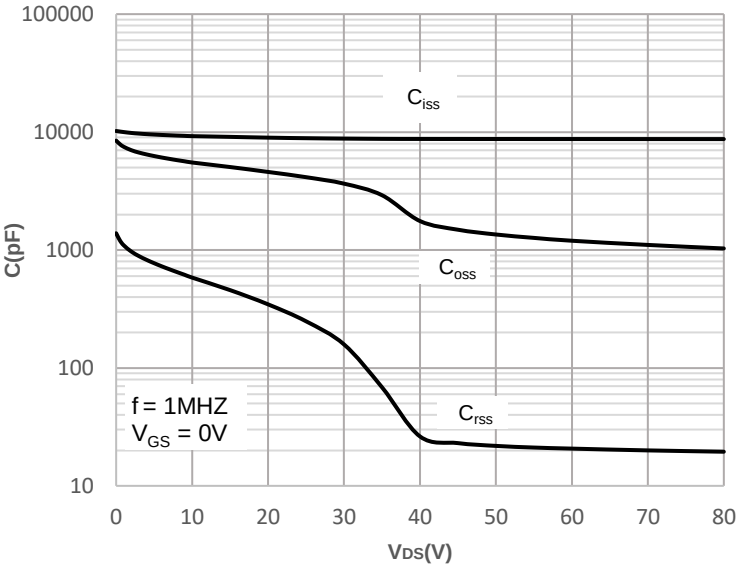


Figure 10: Capacitance Characteristics



Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

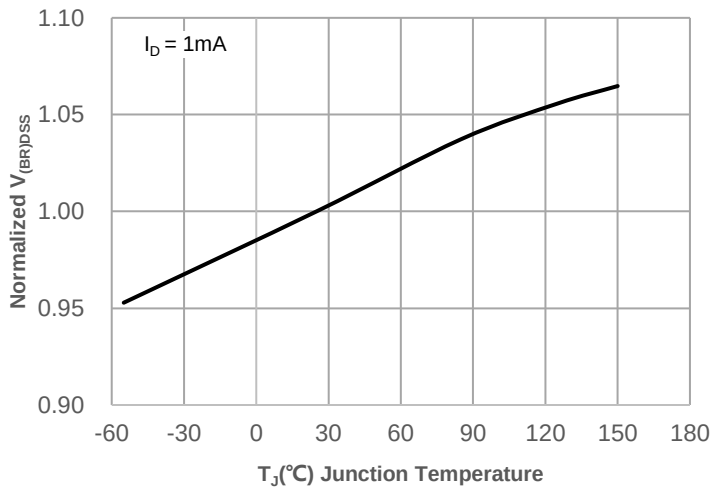


Figure 12: Normalized on Resistance vs. Junction Temperature

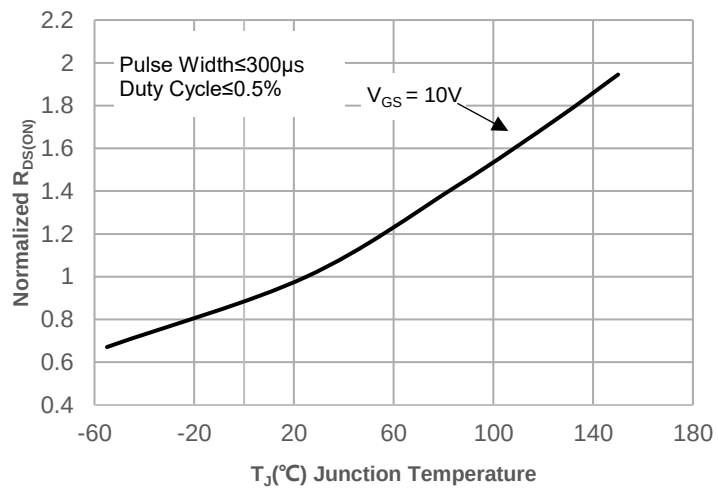


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

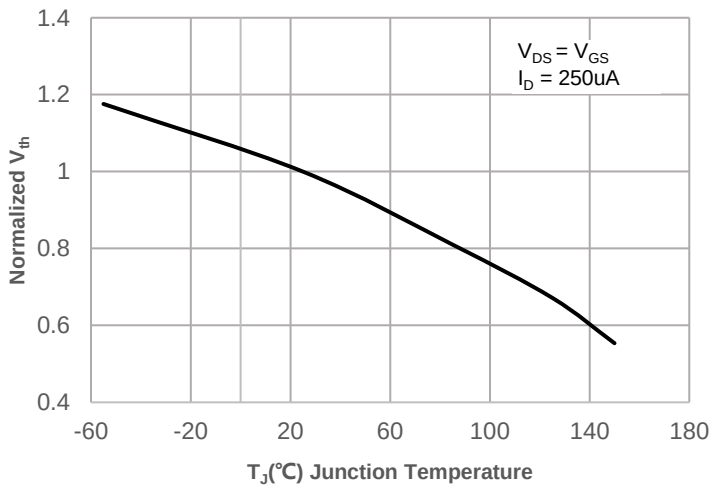


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

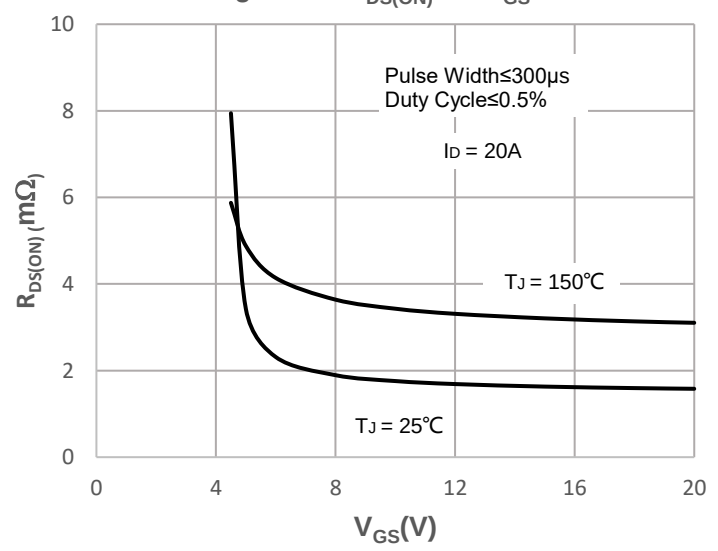
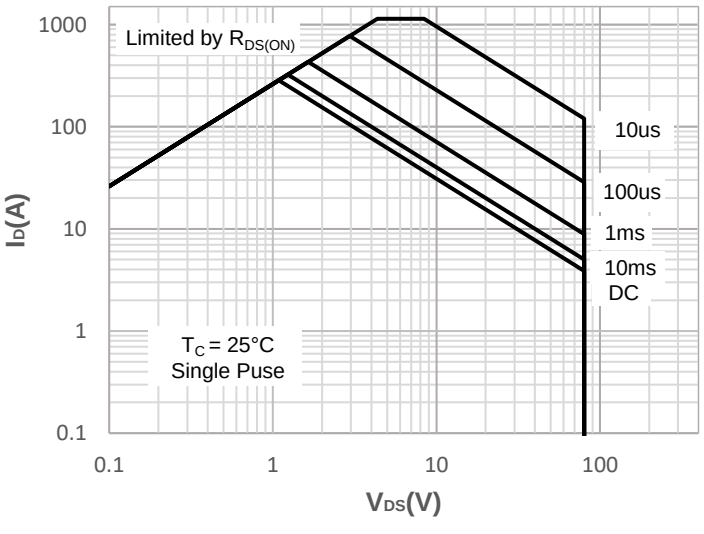


Figure 15: Maximum Safe Operating Area



Test Circuit

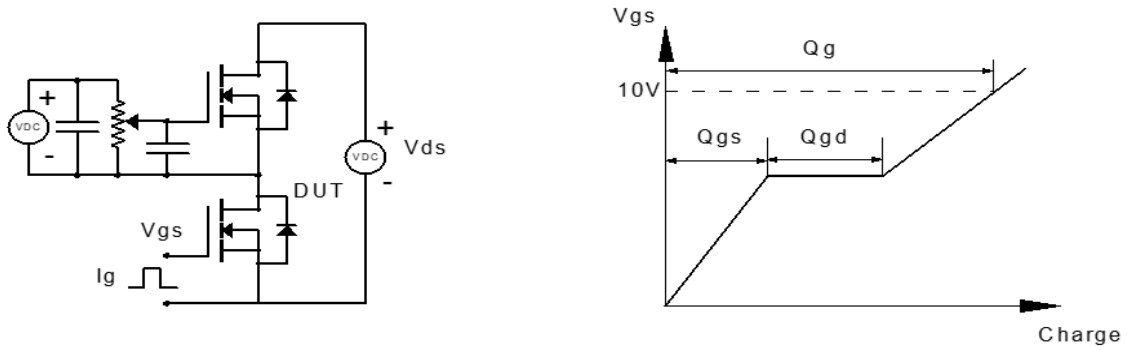


Figure 1: Gate Charge Test Circuit & Waveform

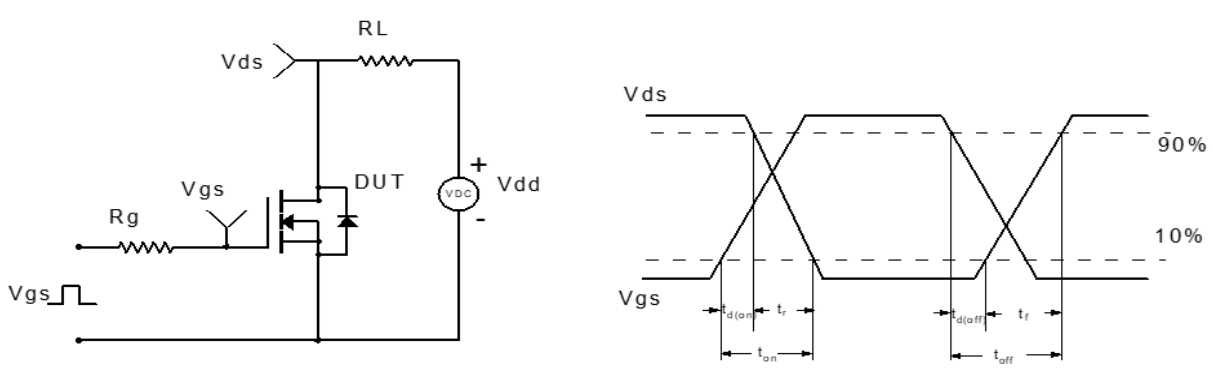


Figure 2: Resistive Switching Test Circuit & Waveform

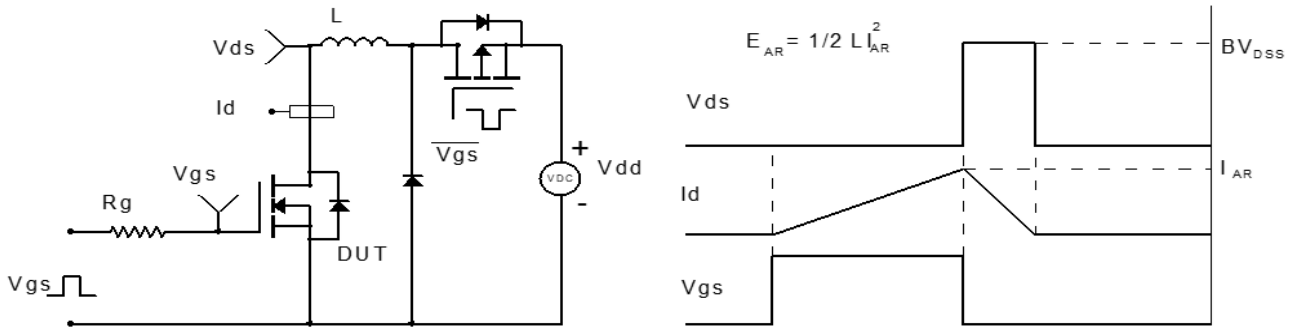


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

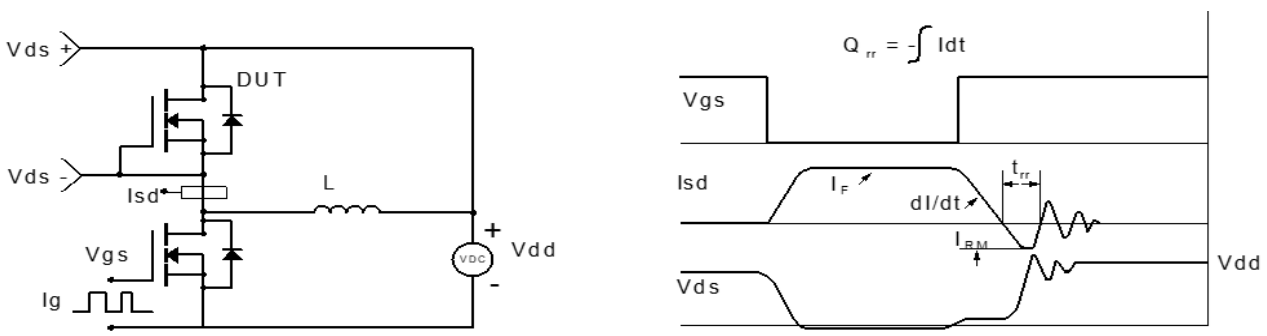
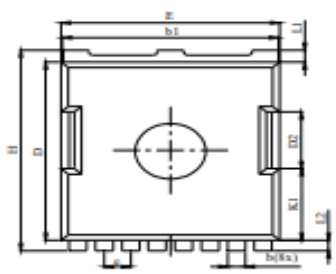


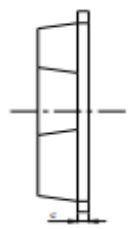
Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(PowerJE®10x12)

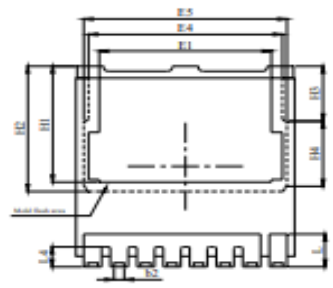
Package Outlines



Top View



Side View



Bottom View

Front View

NOTES:
1. Dimension and tolerance per ASME Y14.5M, 1994.
2. All dimensions in millimeter.
3. Dimensions do not include burrs or mold flash. Mold flash or burrs does not exceed 0.150mm.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.42	0.46	0.50
c	0.40	0.50	0.60
D	10.28	10.38	10.58
D2		3.30	
E	9.70	9.90	10.10
E1		7.80	
E4		8.80	
E5		9.20	
e		1.20 (BSC)	
H	11.48	11.68	11.88
H1	6.55	6.75	6.85
H2		7.30	
H3		3.20	
H4		3.80	
K1		4.18	
L	1.70	1.90	2.10
L1		0.70	
L2		0.60	
L4	1.00	1.15	1.30

Recommended Soldering Footprint